

Single D-Type Flip-Flop With 3-State Output

Check for Samples: [SN74LVC1G374](#)

FEATURES

- Available in the Texas Instruments NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Provides Down Translation to V_{CC}
- Max t_{pd} of 4 ns at 3.3 V
- Low Power Consumption, 10- μ A Max I_{CC}
- ± 24 -mA Output Drive at 3.3 V
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DESCRIPTION

This single D-type latch is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G374 features a 3-state output designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, input/output (I/O) ports, bidirectional bus drivers, and working registers.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

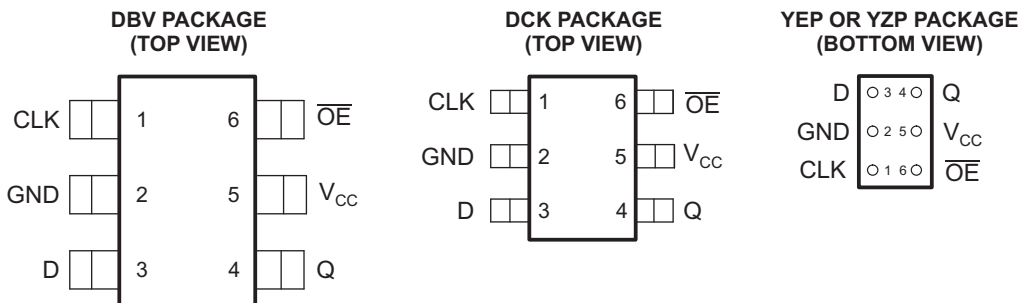
On the positive transition of the clock (CLK) input, the Q output is set to the logic level set up at the data (D) input.

A buffered output-enable (\overline{OE}) input can be used to place the output in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the output neither loads nor drives the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

\overline{OE} does not affect the internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.



See mechanical drawings for dimensions.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar, NanoFree are trademarks of Texas Instruments.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

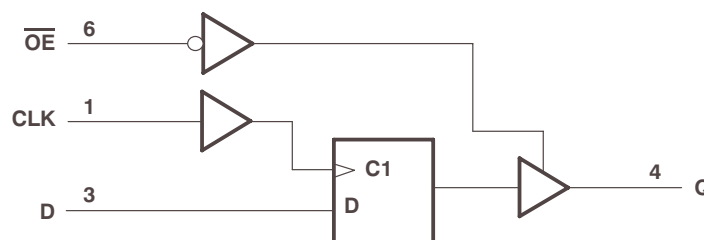
Copyright © 2003–2013, Texas Instruments Incorporated



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Function Table

INPUTS			OUTPUT Q
\overline{OE}	CLK	D	
L	↑	L	L
L	↑	H	H
L	H or L	X	Q
H	X	X	Z

Logic Diagram (Positive Logic)**Absolute Maximum Ratings⁽¹⁾**

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		−0.5	6.5	V
V _I	Input voltage range ⁽²⁾		−0.5	6.5	V
V _O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾		−0.5	6.5	V
V _O	Voltage range applied to any output in the high or low state ⁽²⁾ ⁽³⁾		−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		−50	mA
I _{OK}	Output clamp current	V _O < 0		−50	mA
I _O	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
θ _{JA}	Package thermal impedance ⁽⁴⁾	DBV package		165	°C/W
		DCK package		259	
		YEP/YZP package		123	
T _{std}	Storage temperature range		−65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The value of V_{CC} is provided in the recommended operating conditions table.

(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 3 V to 3.6 V	2		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	0.7		
		V _{CC} = 3 V to 3.6 V	0.8		
		V _{CC} = 4.5 V to 5.5 V	0.3 × V _{CC}		
V _I	Input voltage		0	5.5	V
V _O	Output voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V		–4	mA
		V _{CC} = 2.3 V		–8	
		V _{CC} = 3 V		–16	
				–24	
		V _{CC} = 4.5 V		–32	
I _{OL}	Low-level output current	V _{CC} = 1.65 V		4	mA
		V _{CC} = 2.3 V		8	
		V _{CC} = 3 V		16	
				24	
		V _{CC} = 4.5 V		32	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V _{CC} = 3.3 V ± 0.3 V		10	
		V _{CC} = 5 V ± 0.5 V		5	
T _A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	–40°C to 85°C			–40°C to 125°C			UNIT
			MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	
V _{OH}	I _{OH} = –100 μA	1.65 V to 5.5 V	V _{CC} – 0.1			V _{CC} – 0.1			V
	I _{OH} = –4 mA	1.65 V	1.2			1.2			
	I _{OH} = –8 mA	2.3 V	1.9			1.9			
	I _{OH} = –16 mA	3 V	2.4			2.4			
	I _{OH} = –24 mA		2.3			2.3			
	I _{OH} = –32 mA	4.5 V	3.8			3.8			
V _{OL}	I _{OL} = 100 μA	1.65 V to 5.5 V	0.1			0.1			V
	I _{OL} = 4 mA	1.65 V	0.45			0.45			
	I _{OL} = 8 mA	2.3 V	0.3			0.3			
	I _{OL} = 16 mA	3 V	0.4			0.4			
	I _{OL} = 24 mA		0.55			0.65			
	I _{OL} = 32 mA	4.5 V	0.55			0.65			
I _I	V _I = 5.5 V or GND	0 to 5.5 V	±1			±2			μA
I _{OZ}	V _O = 0 to 5.5 V		±5			±5			μA
I _{off}	V _I or V _O = 5.5 V	0	±10			±10			μA
I _{CC}	V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V	10			10			μA
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V	500			500			μA
C _i	V _I = V _{CC} or GND	3.3 V	3			3			pF
C _o	V _O = V _{CC} or GND	3.3 V	6			6			pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		SN74LVC1G374 –40°C to 85°C								UNIT
		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{clock}	Clock frequency	100		125		150		175		MHz
t _w	Pulse duration, CLK high or low	3.3		3		2.8		2.5		ns
t _{su}	Setup time, data before CLK ↑	3.5		2.5		2		1.5		ns
t _h	Hold time, data after CLK ↑	3.4		1.6		1.5		1.5		ns

Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		SN74LVC1G374 –40°C to 125°C								UNIT
		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{clock}	Clock frequency	100		125		150		175		MHz
t _w	Pulse duration, CLK high or low	3.3		3		2.8		2.5		ns
t _{su}	Setup time, data before CLK ↑	3.5		2.5		2		1.5		ns
t _h	Hold time, data after CLK ↑	3.4		1.6		1.5		1.5		ns

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 15$ pF (unless otherwise noted) (see [Figure 1](#))

PARAMETER	FROM INPUT	TO (OUTPUT)	SN74LVC1G374 –40°C to 85°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			100		125		150		175		MHz
t _{pd}	CLK	Q	2.5	15	2	6	1.4	4	1	3	ns
t _{en}	\overline{OE}	Q	2.2	12	2	4.8	1.3	3.8	1.1	2.5	ns
t _{dis}	\overline{OE}	Q	2.2	11	2	4.8	1.6	4.5	1.2	3.1	ns

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 30$ pF or 50 pF (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM INPUT	TO (OUTPUT)	SN74LVC1G374 –40°C to 85°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			100		125		150		175		MHz
t _{pd}	CLK	Q	2.7	18.3	1.8	8.2	1.6	6	1	4	ns
t _{en}	\overline{OE}	Q	2	13	1.5	6.3	0.9	5	0.7	3.5	ns
t _{dis}	\overline{OE}	Q	2	14	1.1	5.3	1.4	4.5	0.8	3.1	ns

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 30$ pF or 50 pF (unless otherwise noted) (see [Figure 2](#))

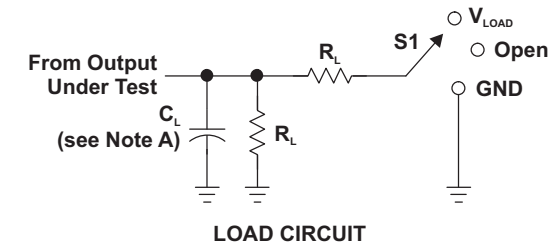
PARAMETER	FROM INPUT	TO (OUTPUT)	SN74LVC1G374 –40°C to 125°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			100		125		150		175		MHz
t _{pd}	CLK	Q	2.7	18.3	1.8	10.2	1.6	7	1	5	ns
t _{en}	\overline{OE}	Q	2	14	1.5	8.3	0.9	6.5	0.7	5.5	ns
t _{dis}	\overline{OE}	Q	2	16	1.1	7.3	1.4	6	0.8	5.1	ns

Operating Characteristics

$T_A = 25^\circ\text{C}$

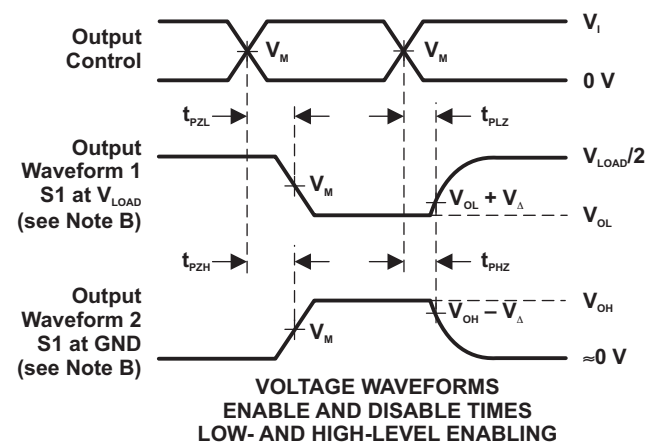
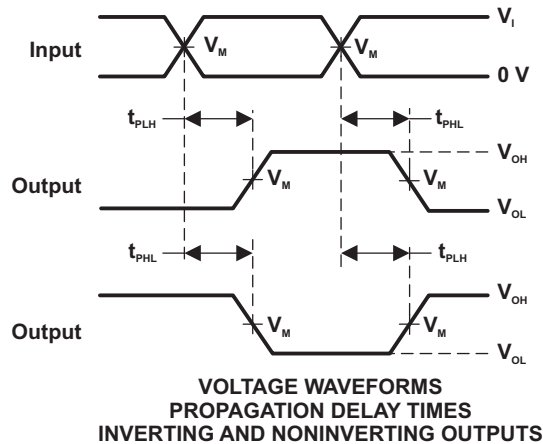
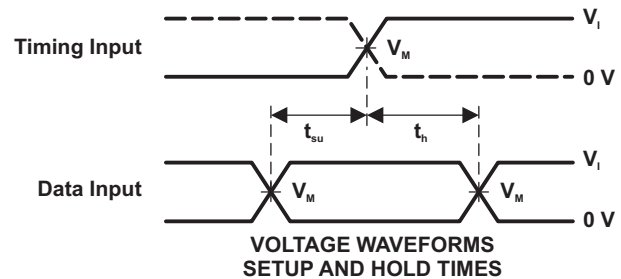
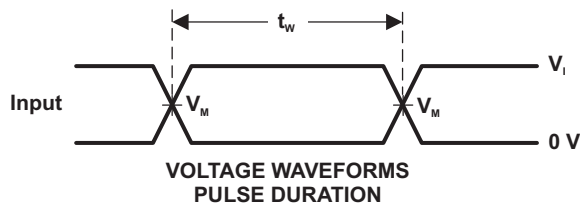
PARAMETER		TEST CONDITIONS	$V_{CC} = 1.8\text{ V}$	$V_{CC} = 2.5\text{ V}$	$V_{CC} = 3.3\text{ V}$	$V_{CC} = 5\text{ V}$	UNIT
			TYP	TYP	TYP	TYP	
C_{pd} Power dissipation capacitance	Outputs enabled	$f = 10\text{ MHz}$	24	24	25	27	pF
	Outputs disabled		8	8	9	11	

PARAMETER MEASUREMENT INFORMATION



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	15 pF	1 M Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_o = 50\ \Omega$.

D. The outputs are measured one at a time, with one transition per measurement.

E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .

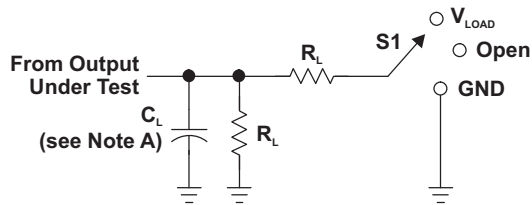
F. t_{PZL} and t_{PZH} are the same as t_{en} .

G. t_{PLH} and t_{PHL} are the same as t_{pd} .

H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

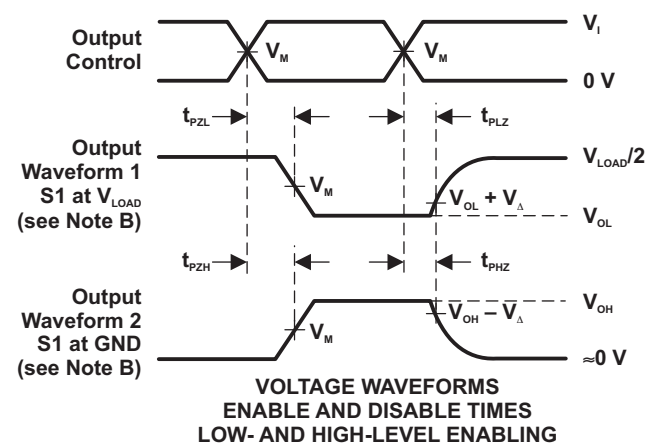
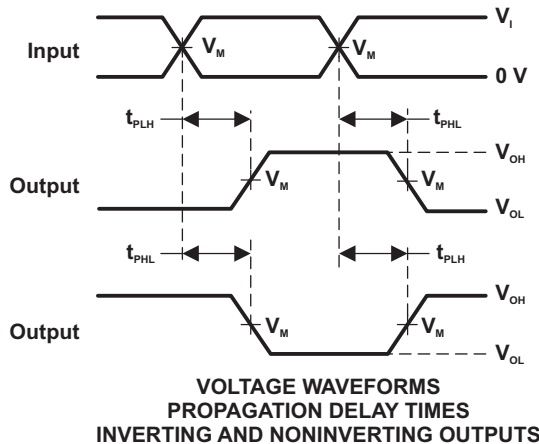
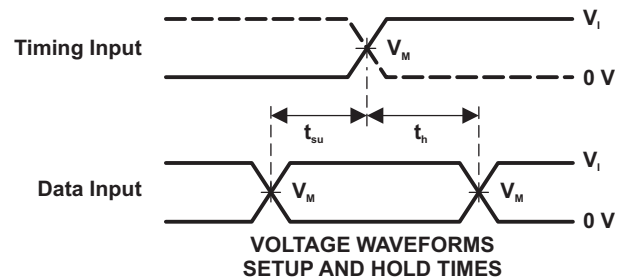
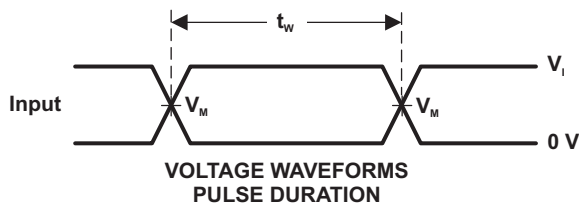
PARAMETER MEASUREMENT INFORMATION (continued)



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_o = 50\text{ }\Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{on} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

REVISION HISTORY

Changes from Revision B (September 2006) to Revision C	Page
• Updated document to new TI data sheet format.	1
• Removed Ordering Information table.	2
• Added ESD warning.	2
• Updated operating temperature range.	3

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74LVC1G374DCKRG4	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D45
74LVC1G374DCKRG4.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D45
SN74LVC1G374DBVR	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CA45, CA4R)
SN74LVC1G374DBVR.B	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CA45, CA4R)
SN74LVC1G374DCKR	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU SN NIPDAU	Level-1-260C-UNLIM	-40 to 125	(D45, D4J, D4R)
SN74LVC1G374DCKR.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(D45, D4J, D4R)
SN74LVC1G374DCKRG4.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
SN74LVC1G374YZPR	Active	Production	DSBGA (YZP) 6	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	D4N
SN74LVC1G374YZPR.B	Active	Production	DSBGA (YZP) 6	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	D4N

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative

and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G374 :

- Automotive : [SN74LVC1G374-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



*All dimensions are nominal

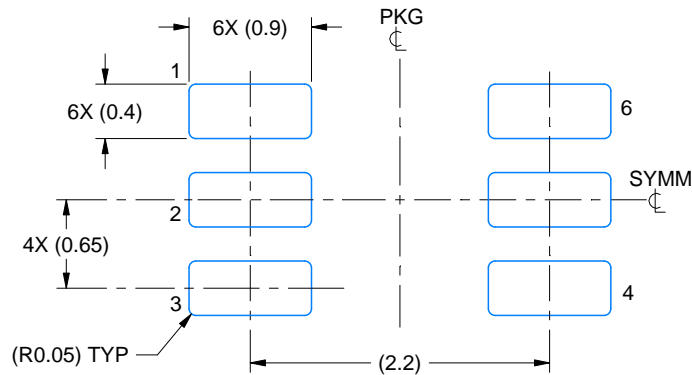
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G374DCKRG4	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G374DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G374DBVR	SOT-23	DBV	6	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G374DCKR	SC70	DCK	6	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC1G374YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

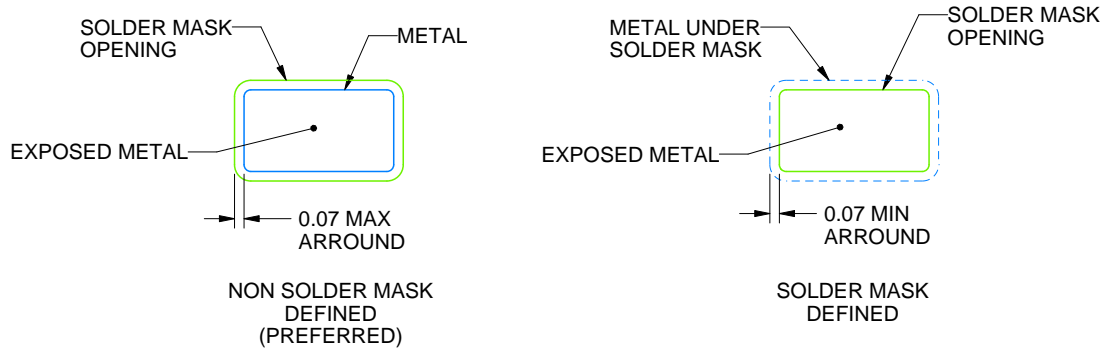


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G374DCKRG4	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1G374DBVR	SOT-23	DBV	6	3000	202.0	201.0	28.0
SN74LVC1G374DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC1G374DCKR	SC70	DCK	6	3000	210.0	185.0	35.0
SN74LVC1G374YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214835/D 11/2024

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 THICK STENCIL
 SCALE:18X

4214835/D 11/2024

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.



SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



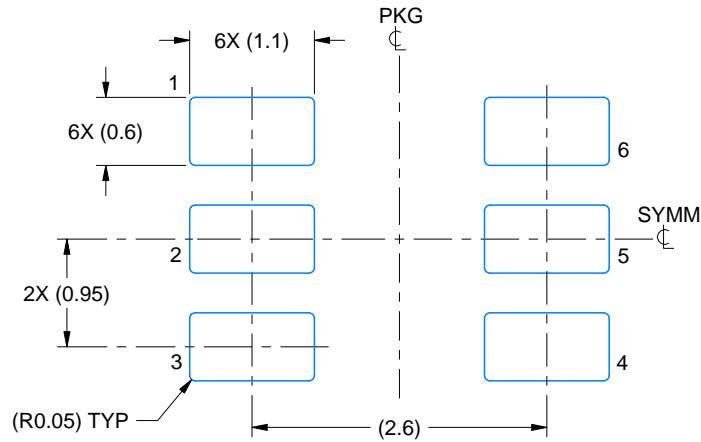
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Reference JEDEC MO-178.

EXAMPLE BOARD LAYOUT

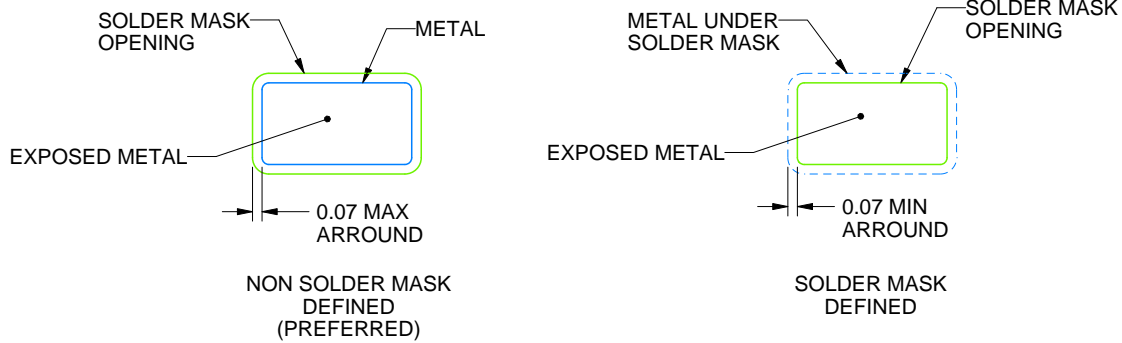
DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214840/G 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214840/G 08/2024

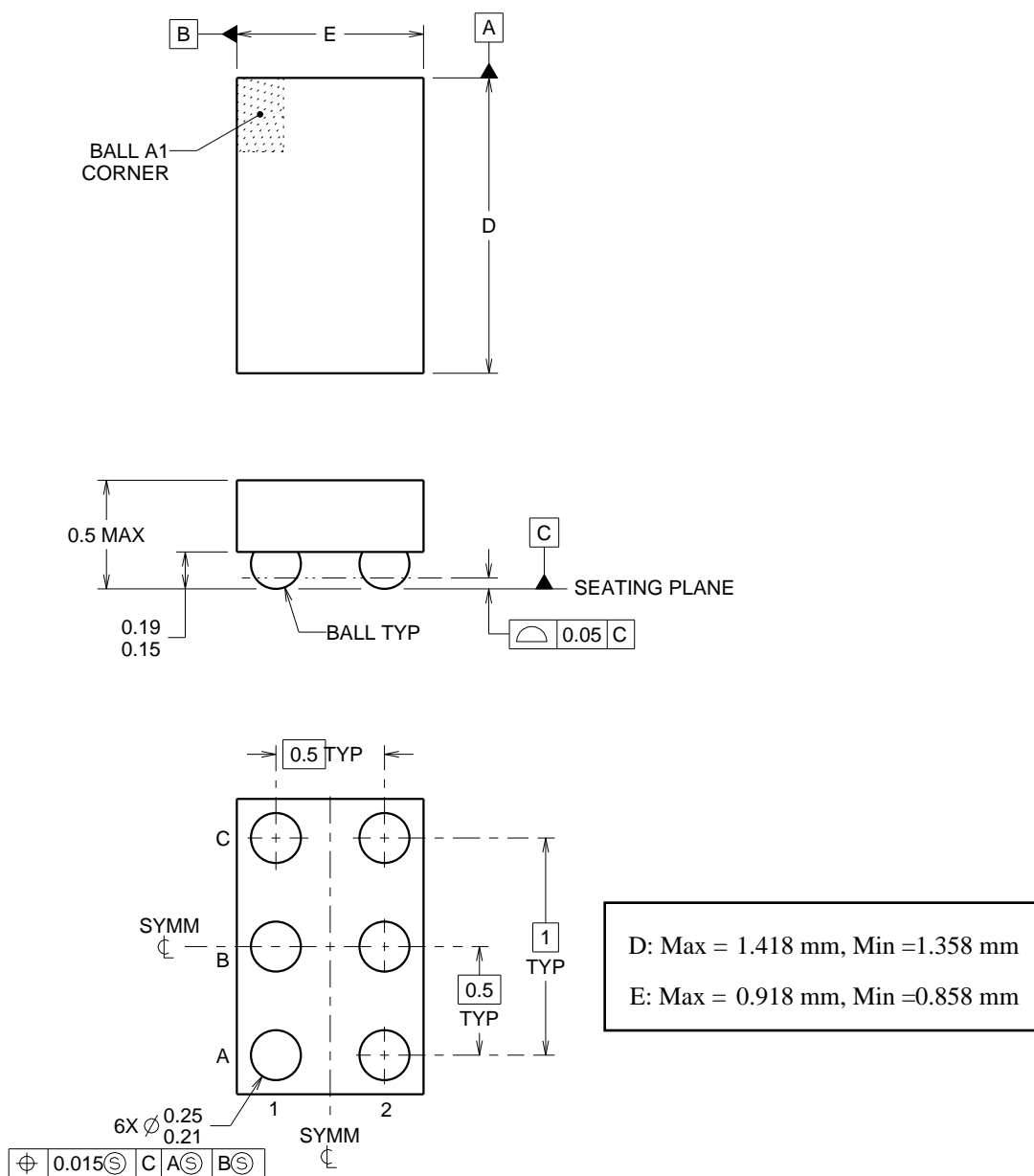
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



4219524/A 06/2014

NOTES:

NanoFree Is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. NanoFree™ package configuration.

EXAMPLE BOARD LAYOUT

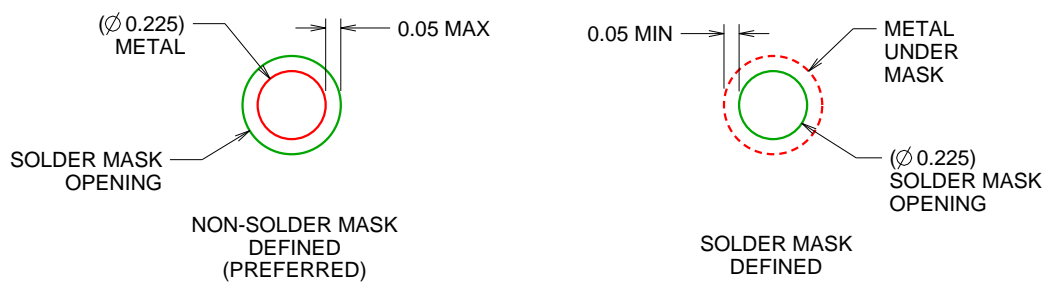
YZP0006

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

4219524/A 06/2014

NOTES: (continued)

- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).

EXAMPLE STENCIL DESIGN

YZP0006

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4219524/A 06/2014

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to [TI's Terms of Sale](#) or other applicable terms available either on [ti.com](https://www.ti.com) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2025, Texas Instruments Incorporated